

2SC4787

Silicon NPN epitaxial planer type

For intermediate frequency amplification

Features

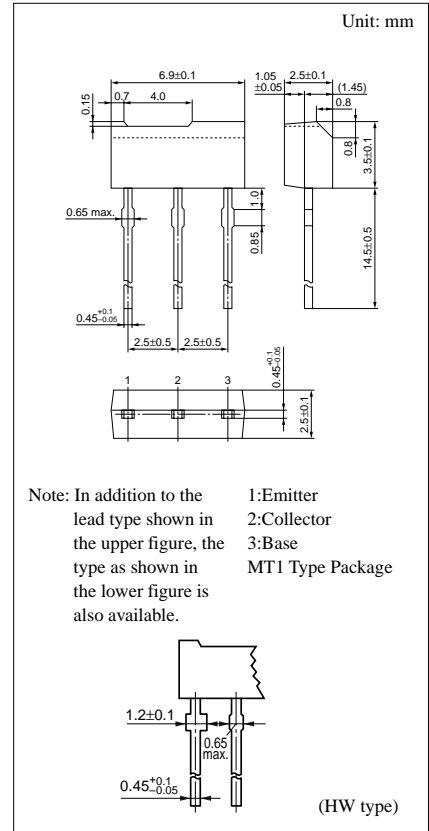
- High transition frequency f_T .
- Satisfactory linearity of forward current transfer ratio h_{FE} .
- Allowing supply with the radial taping.

Absolute Maximum Ratings (Ta=25°C)

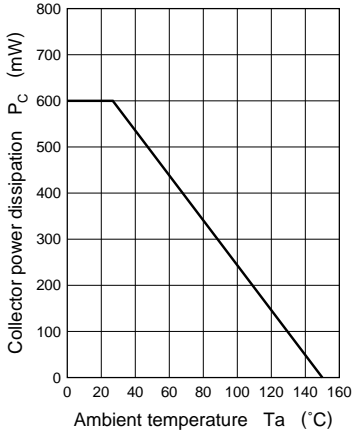
Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	45	V
Collector to emitter voltage	V_{CEO}	35	V
Emitter to base voltage	V_{EBO}	4	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	600	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

Electrical Characteristics (Ta=25°C)

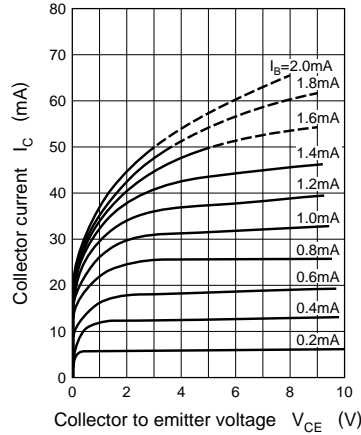
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 20V, I_E = 0$			0.1	μA
Collector to base voltage	V_{CBO}	$I_C = 100\mu A, I_E = 0$	45			V
Collector to emitter voltage	V_{CEO}	$I_C = 1mA, I_B = 0$	35			V
Emitter to base voltage	V_{EBO}	$I_E = 100\mu A, I_C = 0$	4			V
Forward current transfer ratio	h_{FE}	$V_{CE} = 10V, I_C = 10mA$	20	50	100	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 20mA, I_B = 2mA$			0.5	V
Common emitter reverse transfer capacitance	C_{re}	$V_{CB} = 10V, I_E = -1mA, f = 10.7MHz$			1.5	pF
Power gain	PG	$V_{CB} = 10V, I_E = -10mA, f = 58MHz$	18			dB
Transition frequency	f_T	$V_{CB} = 10V, I_E = -10mA, f = 100MHz$	300	500		MHz



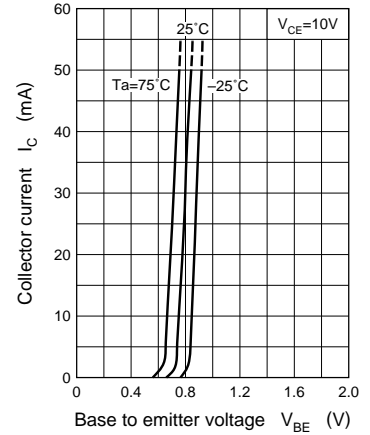
$P_C - T_a$



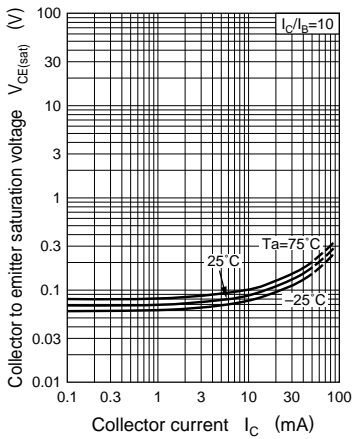
$I_C - V_{CE}$



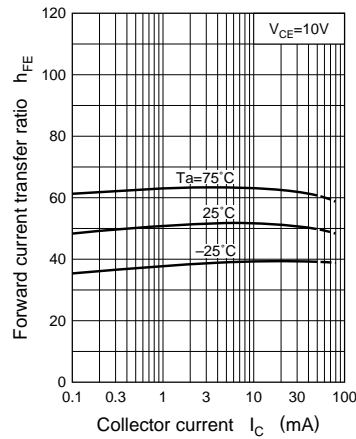
$I_C - V_{BE}$



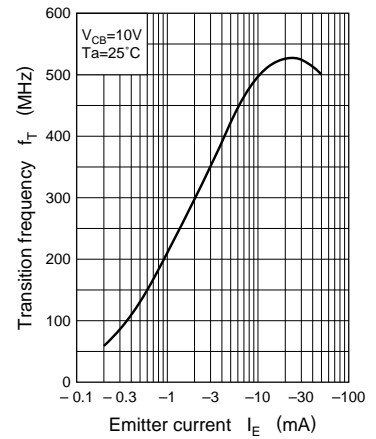
$V_{CE(sat)} - I_C$



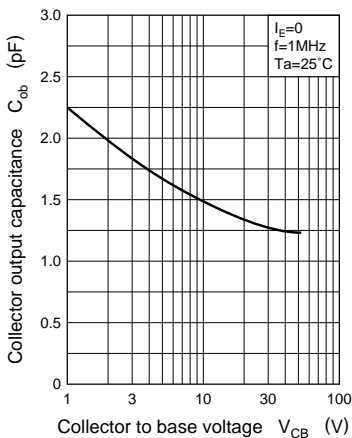
$h_{FE} - I_C$



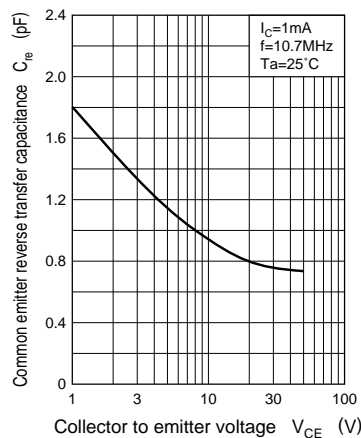
$f_T - I_E$



$C_{ob} - V_{CB}$



$C_{re} - V_{CE}$



$PG - I_E$

